



#12/C (NE)  
12-9-02  
Mullish

Attorney Docket: P-1164-US2

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

12/17/02  
Mullish

Applicant: Boaz EITAN Examiner: C. Chaudhari  
Serial No.: 09/966,754 Group Art Unit: 2813  
Filed: July 30, 1999  
Title: AN NROM FABRICATION METHOD

**AMENDMENT**

Assistant Commissioner for Patents  
Washington, DC 20231

RECEIVED  
DEC -5 2002  
TECHNOLOGY CENTER 2800

Sir:

This Amendment is filed in response to the Office Action dated June 18, 2002 issued by the United States Patent and Trademark Office in connection with the above-identified Application. A response to the Office Action was due September 18, 2002. Applicant is concurrently filing a Petition for a Three-Month Extension of Time, including the required fee. Therefore, a response is due December 18, 2002. Accordingly, this Amendment is being timely filed.

Kindly amend the above-identified application as follows:

**In the Claims**

Kindly amend claims 1, 4, 5 and 7 to read as follows:

903 7  
307  
C1  
--1. (Once amended) A method of fabricating an oxide-nitride-oxide (ONO) layer in a memory cell, said method comprising:

forming a bottom oxide layer on a substrate;

depositing a nitride layer; and

oxidizing a top oxide layer, thereby causing oxygen to be introduced into substantially all of said nitride layer within said memory cell, so as to enhance charge retention within said nitride layer.